

SN. 10/720,738

ATTORNEY DOCKET NO. FUJI:280

second trench section intersecting the first trench section to form a mesh pattern surrounding the non-trench region.

wherein the first diffusion region is formed at the bottom of the first trench section, and

wherein the semiconductor device is a trench lateral transistor composed of at least the semiconductor substrate, the first and second diffusion regions, the first diffusion region driving current as a transistor, a gate insulator film formed inside the trench, a first conductor formed inside the gate insulator film, a second conductor formed inside the first conductor in the active region with an interlayer insulator film interposed therebetween and electrically connected to the first diffusion region, a first electrode penetrating through the interlayer insulator film electrically connected to the second diffusion region, and a second electrode penetrating through the interlayer insulator film to electrically connect to the second conductor.

9-12. (Canceled)

13. (Currently Amended) The semiconductor device as claimed in claim [[8]]1, wherein the second diffusion region is a drain region and the first diffusion region is a source region.

14. (Currently Amended) The semiconductor device as claimed in claim [[8]]1, wherein the second diffusion region is a source region and the first diffusion region is a drain region.

15. (Currently Amended) The semiconductor device as claimed in claim [[13]]1, further including a first electrode electrically connected to the second diffusion region, wherein the inside of the third trench section is filled with the first conductor with [[the]]a gate insulator film interposed therebetween, and the first conductor in the third trench section and the first electrode are insulated from each other by an interlayer insulator film.

16. (Canceled)

17. (Currently Amended) The semiconductor device as claimed in claim [[8]]~~25~~, wherein an

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